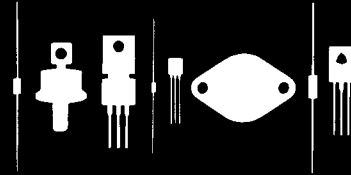


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2N6473 2N6474 NPN
2N6475 2N6476 PNP

COMPLEMENTARY SILICON
SWITCHING TRANSISTORS

JEDEC TO-220 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N6473 Series types are complementary silicon power transistors manufactured by the epitaxial base process designed for general purpose amplifier and switching applications.

MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

	SYMBOL	2N6473	2N6474	UNIT
		2N6475	2N6476	
Collector-Base Voltage	V _{CB0}	110	130	V
Collector-Emitter Voltage (R _{BE} =100Ω)	V _{CER}	110	130	V
Collector-Emitter Voltage	V _{CEO}	100	120	V
Emitter-Base Voltage	V _{EBO}		5.0	V
Collector Current	I _C		4.0	A
Base Current	I _B		2.0	A
Power Dissipation	P _D		40	W
Operating and Storage Junction Temperature	T _J , T _{stg}		-65 TO +150	°C
Thermal Resistance	θ _{JC}		3.125	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N6473		2N6474		UNIT	
		2N6475	MIN	MAX	MIN		MAX
I _{CEV}	V _{CE} =Rated V _{CEO} , V _{BE} =1.5V			0.1		0.1	mA
I _{CEV}	V _{CE} =Rated V _{CEO} , V _{BE} =1.5V, T _C =100°C			2.0		2.0	mA
I _{CER}	V _{CE} =Rated V _{CER} , R _{BE} =100Ω			0.1		0.1	mA
I _{CER}	V _{CE} =Rated V _{CER} , R _{BE} =100Ω, T _C =100°C			2.0		2.0	mA
I _{CEO}	V _{CE} =½ Rated V _{CEO}			1.0		1.0	mA
I _{EBO}	V _{BE} =5.0V			1.0		1.0	mA
BV _{CEO}	I _C =100mA	100			120		V
BV _{CER}	I _C =100mA, R _{BE} =100Ω	110			130		V
V _{CE} (SAT)	I _C =1.5A, I _B =0.15A			1.2		1.2	V
V _{CE} (SAT)	I _C =4.0A, I _B =2.0A			2.5		2.5	V
V _{BE} (ON)	V _{CE} =4.0V, I _C =1.5A			2.0		2.0	V
V _{BE} (ON)	V _{CE} =2.5V, I _C =4.0A			3.5		3.5	V
h _{FE}	V _{CE} =4.0V, I _C =1.5A		15	150		15	150
h _{FE}	V _{CE} =2.5V, I _C =4.0A		2.0			2.0	
h _{fe}	V _{CE} =4.0V, I _C =0.5A, f=50kHz		20			20	
f _T	V _{CE} =4.0V, I _C =0.5A (2N6473, 2N6474)		4.0			4.0	MHz
f _T	V _{CE} =4.0V, I _C =0.5A (2N6475, 2N6476)		5.0			5.0	MHz
C _{ob}	V _{CB} =10V, f=1.0MHz			250		250	pF